


Fast Recovery Diodes (T-Modules), 40 A/70 A/85 A



D-55

FEATURES

- Fast recovery time characteristics
- Electrically isolated base plate
- 3500 V_{RMS} isolating voltage
- Standard JEDEC package
- Simplified mechanical designs, rapid assembly
- Large creepage distances
- UL E78996 approved 
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level



RoHS
COMPLIANT

DESCRIPTION

The series of T-modules uses fast recovery power diodes in a single diode configuration. The semiconductors are electrically isolated from the metal base, allowing common heatsink and compact assemblies to be built.

These single diode modules can be used in conjunction with the thyristor modules as a freewheel diode. Application includes self-commutated inverters, DC choppers, motor control, inductive heating and electronic welders. These modules are intended for those applications where very fast recovery characteristics are required and for general power switching applications.

PRODUCT SUMMARY

$I_{F(AV)}$	40 A/70 A/85 A
Type	Modules - Diode, Fast

MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	T40HFL	T70HFL	T85HFL	UNITS
$I_{F(AV)}$		40	70	85	A
$I_{F(RMS)}$		63	110	133	A
I_{FSM}	50 Hz	475	830	1300	A
	60 Hz	500	870	1370	
I^2t	50 Hz	1130	3460	8550	A ² s
	60 Hz	1030	3160	7810	
V_{RRM}	Range	100 to 1000			V
t_{rr}	Range	200 to 1000			ns
T_J	Range	- 40 to 125			°C

T40HFL, T70HFL, T85HFL Series



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Fast Recovery Diodes
(T-Modules), 40 A/70 A/85 A

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS					
TYPE NUMBER	VOLTAGE CODE	t_{rr} CODE	V_{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} MAXIMUM AT $T_J = 25^\circ\text{C}$ μA
T40HFL.. T70HFL.. T85HFL..	10	S02, S05, S10	100	150	100
	20	S02, S05, S10	200	300	
	40	S02, S05, S10	400	500	
	60	S02, S05, S10	600	700	
	80	S05, S10	800	900	
	100	S05, S10	1000	1100	

FORWARD CONDUCTION								
PARAMETER	SYMBOL	TEST CONDITIONS			T40HFL	T70HFL	T85HFL	UNITS
Maximum average forward current at case temperature	$I_{F(AV)}$	180° conduction, half sine wave			40	70	85	A
					70			°C
Maximum RMS forward current	$I_{F(RMS)}$				63	110	133	A
Maximum peak, one-cycle forward, non-repetitive surge current	I_{FSM}	t = 10 ms	No voltage reappplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	475	830	1300	A
		t = 8.3 ms			500	870	1370	
		t = 10 ms	100 % V_{RRM} reappplied		400	700	1100	
		t = 8.3 ms			420	730	1150	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reappplied		1130	3460	8550	A ² s
		t = 8.3 ms			1030	3160	7810	
		t = 10 ms	100 % V_{RRM} reappplied		800	2450	6050	
		t = 8.3 ms			730	2230	5520	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 ms to 10 ms, no voltage reappplied			11 300	34 600	85 500	A ² √s
Low level value of threshold voltage	$V_{F(TO)1}$	$T_J = 25^\circ\text{C}$, $(16.7\% \times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)})$			0.82	0.87	0.84	V
High level value of threshold voltage	$V_{F(TO)2}$	$T_J = 25^\circ\text{C}$, $(I > \pi \times I_{F(AV)})$			0.84	0.90	0.86	
Low level value of forward slope resistance	r_{f1}	$T_J = 25^\circ\text{C}$, $(16.7\% \times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)})$			7.0	2.77	2.15	mΩ
High level value of forward slope resistance	r_{f2}	$T_J = 25^\circ\text{C}$, $(I > \pi \times I_{F(AV)})$			6.8	2.67	2.07	
Maximum forward voltage drop	V_{FM}	$I_{FM} = \pi \times I_{F(AV)}$, $T_J = 25^\circ\text{C}$, $t_p = 400 \mu\text{s}$ square wave Average power = $V_{F(TO)} \times I_{F(AV)} + r_f \times (I_{F(RMS)})^2$			1.60	1.73	1.55	V



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REVERSE RECOVERY CHARACTERISTICS												
PARAMETER	SYMBOL	TEST CONDITIONS ⁽¹⁾	T40HFL			T70HFL			T85HFL			UNITS
			S02	S05	S10	S02	S05	S10	S02	S05	S10	
Maximum reverse recovery time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}$, $-di_F/dt = 100\text{ A}/\mu\text{s}$ $I_F = 1\text{ A}$ to $V_R = 30\text{ V}$	70	110	270	70	110	270	80	120	290	ns
		$T_J = 25\text{ }^\circ\text{C}$, $-di_F/dt = 25\text{ A}/\mu\text{s}$ $I_{FM} = \pi \times \text{rated } I_{F(AV)}$, $V_R = -30\text{ V}$	200	500	1000	200	500	1000	200	500	1000	
Maximum reverse recovery charge	Q_{rr}	$T_J = 25\text{ }^\circ\text{C}$, $-di_F/dt = 100\text{ A}/\mu\text{s}$ $I_F = 1\text{ A}$ to $V_R = 30\text{ V}$	0.25	0.4	1.35	0.25	0.4	1.35	0.3	0.6	1.6	μC
		$T_J = 25\text{ }^\circ\text{C}$, $-di_F/dt = 25\text{ A}/\mu\text{s}$ $I_{FM} = \pi \times \text{rated } I_{F(AV)}$, $V_R = -30\text{ V}$	0.55	2.0	8.0	0.6	2.1	8.5	0.8	3.5	1.5	

Note

⁽¹⁾ Tested on LEM 300 A diodometer tester

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	T40HFL	T70HFL	T85HFL	UNITS
Maximum peak reverse leakage current	I_{RRM}	$T_J = 125\text{ }^\circ\text{C}$	20			mA
RMS isolation voltage	V_{ISOL}	50 Hz, circuit to base, all terminals shorted, $T_J = 25\text{ }^\circ\text{C}$, $t = 1\text{ s}$	3500			V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	T40HFL	T70HFL	T85HFL	UNITS
Junction operating temperature range	T_J		- 40 to 125			$^\circ\text{C}$
Storage temperature range	T_{Stg}		- 40 to 150			
Maximum internal thermal resistance, junction to case per module	R_{thJC}	DC operation	0.85	0.53	0.46	K/W
Thermal resistance, case to heatsink per module	R_{thCS}	Mounting surface, flat, smooth and greased	0.2			
Mounting torque $\pm 10\%$	base to heatsink	M3.5 mounting screws ⁽¹⁾ Non-lubricated threads	1.3 $\pm 10\%$			Nm
	busbar to terminal	M5 screws terminals Non-lubricated threads	3 $\pm 10\%$			
Approximate weight		See dimensions - link at the end of datasheet	54			g
			19			oz.
Case style			D-55 (T-module)			

Note

⁽¹⁾ A mounting compound is recommended and the torque should be rechecked after a period of about 3 hours to allow for the spread of the compound

ΔR CONDUCTION											
DEVICES	SINUSOIDAL CONDUCTION AT T_J MAXIMUM					RECTANGULAR CONDUCTION AT T_J MAXIMUM					UNITS
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
T40HFL	0.06	0.08	0.10	0.14	0.24	0.05	0.08	0.10	0.15	0.24	K/W
T70HFL	0.05	0.06	0.08	0.11	0.19	0.04	0.06	0.08	0.12	0.19	
T85HFL	0.04	0.05	0.06	0.09	0.15	0.03	0.05	0.07	0.09	0.015	

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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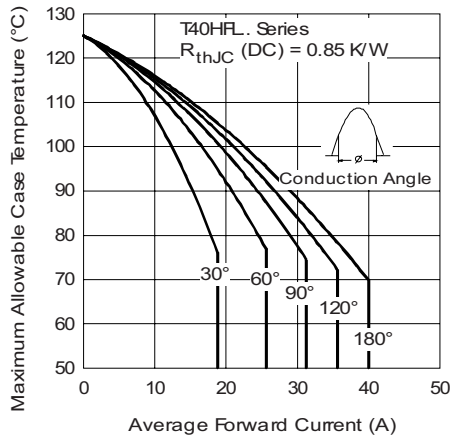


Fig. 1 - Current Ratings Characteristics

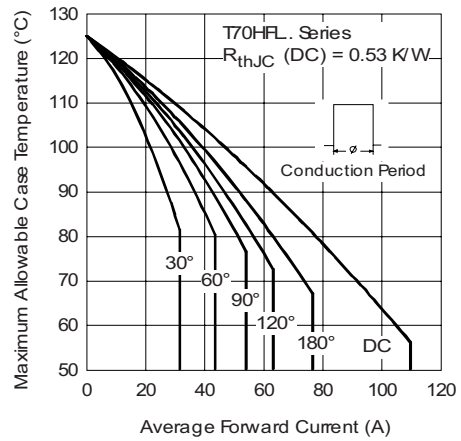


Fig. 4 - Current Ratings Characteristics

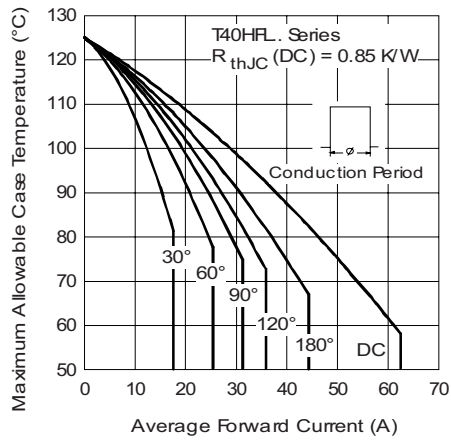


Fig. 2 - Current Ratings Characteristics

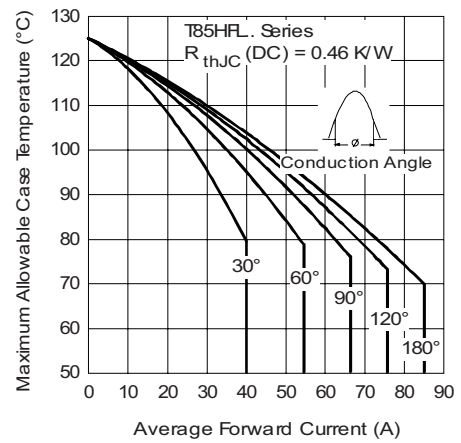


Fig. 5 - Current Ratings Characteristics

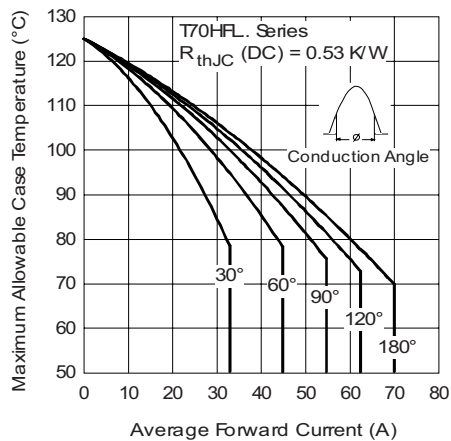


Fig. 3 - Current Ratings Characteristics

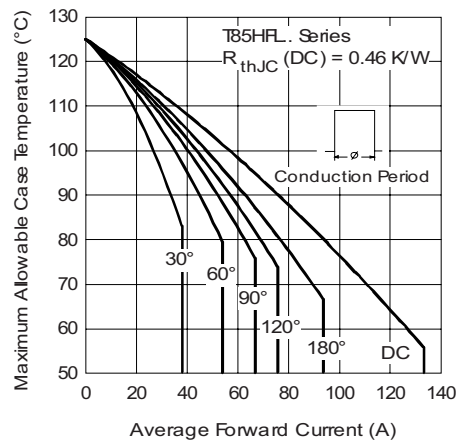


Fig. 6 - Current Ratings Characteristics



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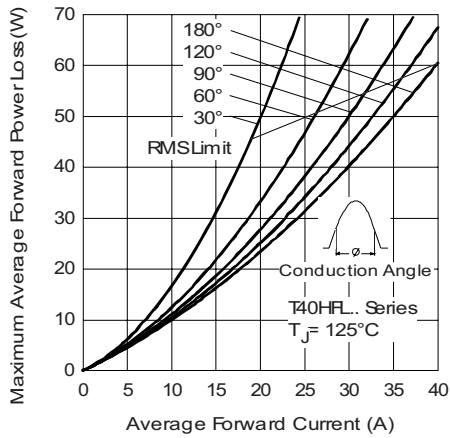


Fig. 7 - Forward Power Loss Characteristics

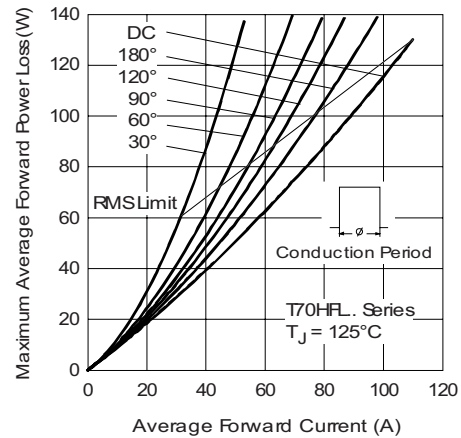


Fig. 10 - Forward Power Loss Characteristics

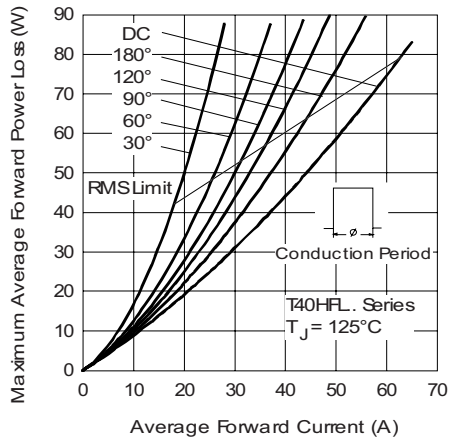


Fig. 8 - Forward Power Loss Characteristics

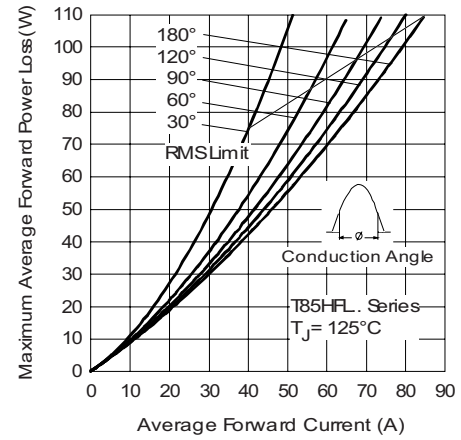


Fig. 11 - Forward Power Loss Characteristics

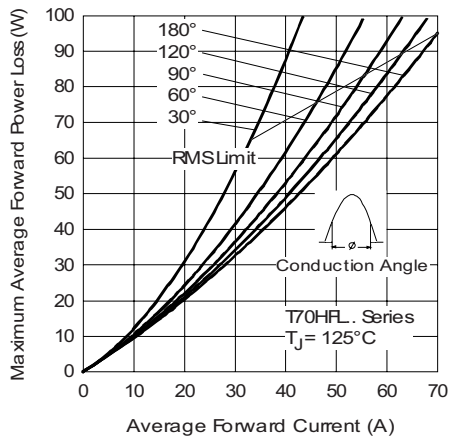


Fig. 9 - Forward Power Loss Characteristics

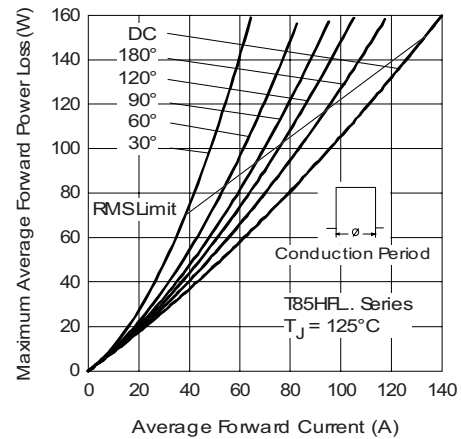


Fig. 12 - Forward Power Loss Characteristics

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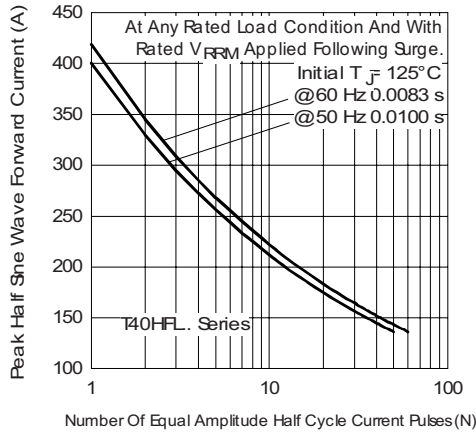


Fig. 13 - Maximum Non-Repetitive Surge Current

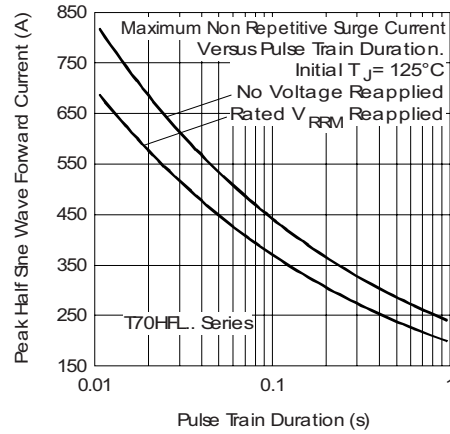


Fig. 16 - Maximum Non-Repetitive Surge Current

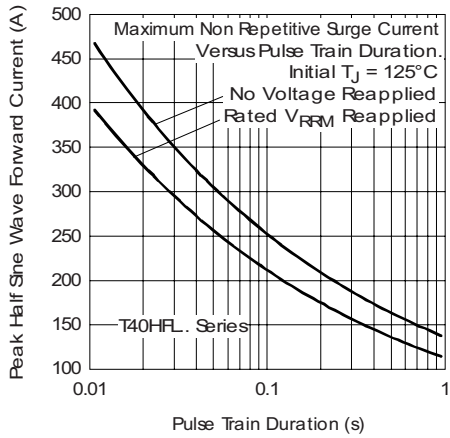


Fig. 14 - Maximum Non-Repetitive Surge Current

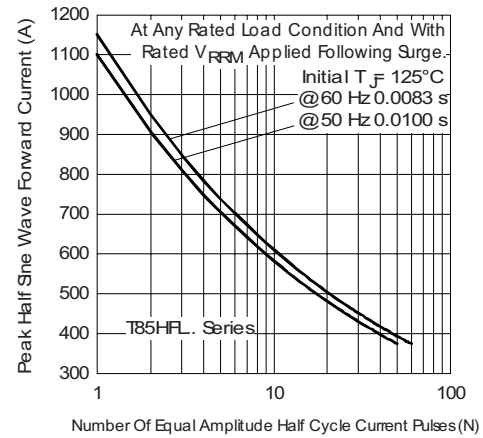


Fig. 17 - Maximum Non-Repetitive Surge Current

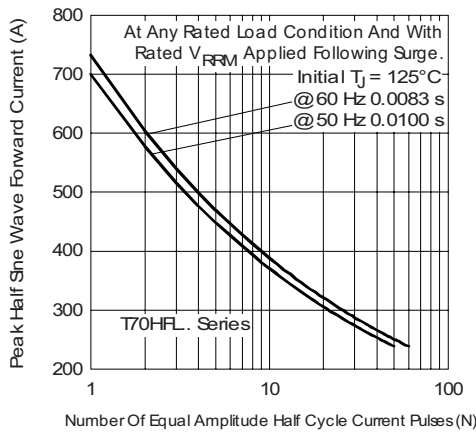


Fig. 15 - Maximum Non-Repetitive Surge Current

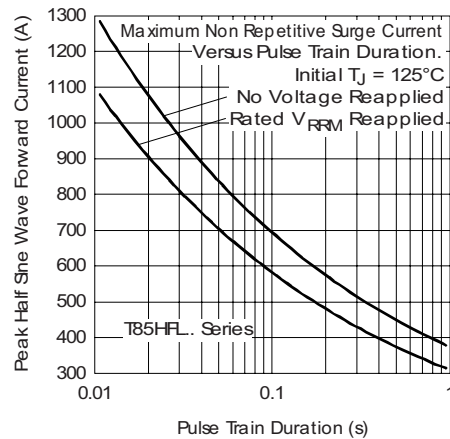


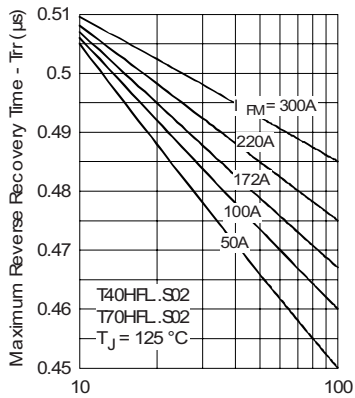
Fig. 18 - Maximum Non-Repetitive Surge Current



T40HFL, T70HFL, T85HFL Series

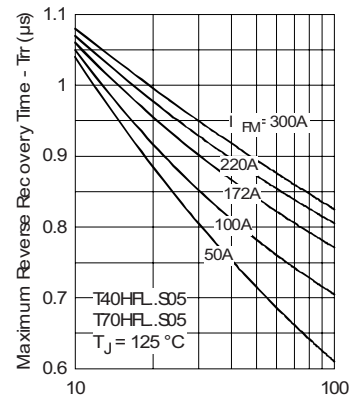
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Rate Of Fall Of Forward Current - di/dt (A/μs)

Fig. 19 - Recovery Time Characteristics



Rate Of Fall Of Forward Current - di/dt (A/μs)

Fig. 22 - Recovery Time Characteristics

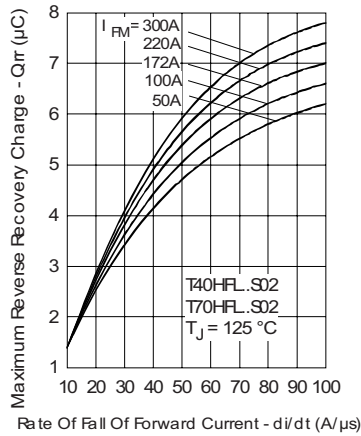


Fig. 20 - Recovery Charge Characteristics

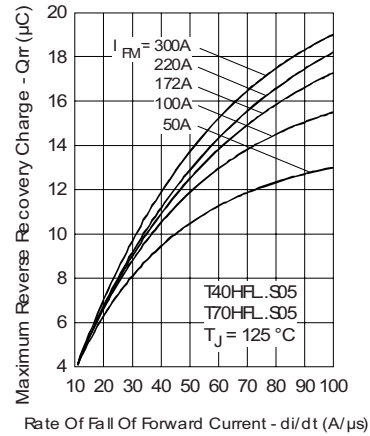


Fig. 23 - Recovery Charge Characteristics

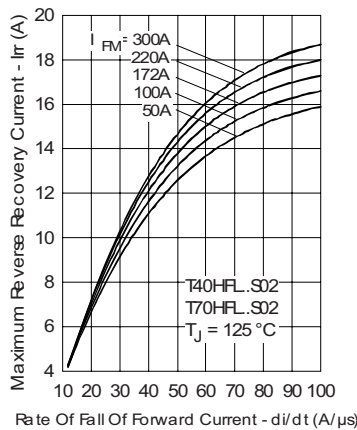


Fig. 21 - Recovery Current Characteristics

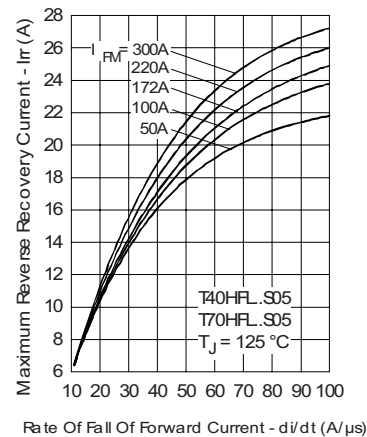


Fig. 24 - Recovery Current Characteristics

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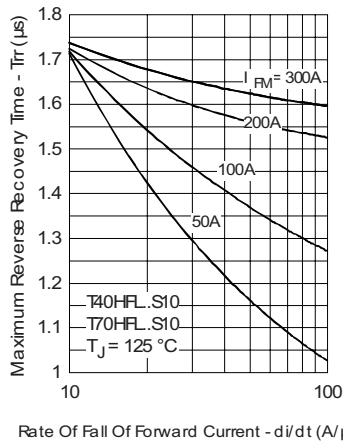


Fig. 25 - Recovery Time Characteristics

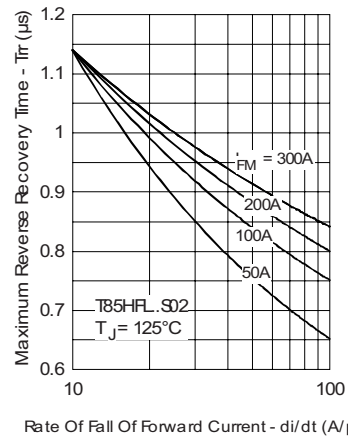


Fig. 28 - Recovery Time Characteristics

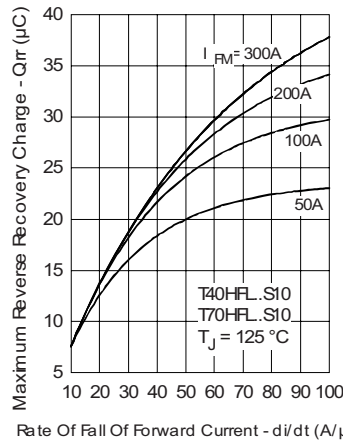


Fig. 26 - Recovery Charge Characteristics

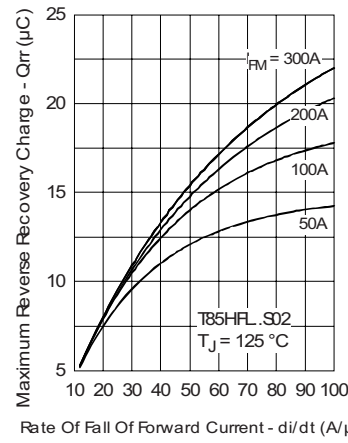


Fig. 29 - Recovery Charge Characteristics

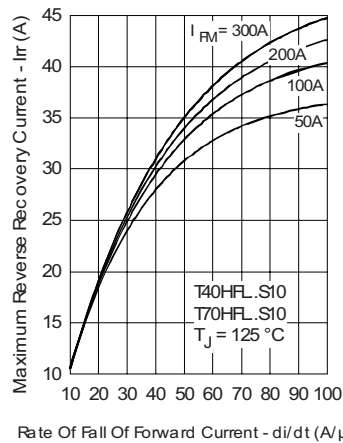


Fig. 27 - Recovery Current Characteristics

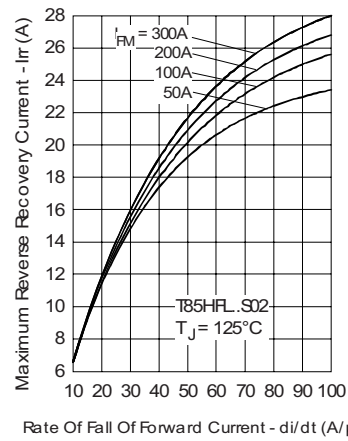


Fig. 30 - Recovery Current Characteristics



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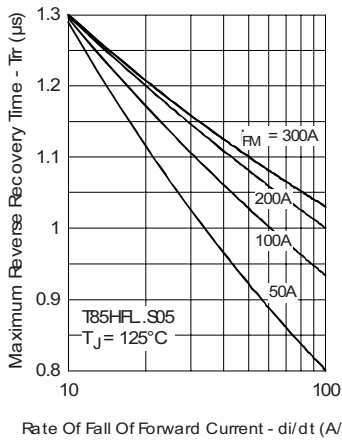


Fig. 31 - Recovery Time Characteristics

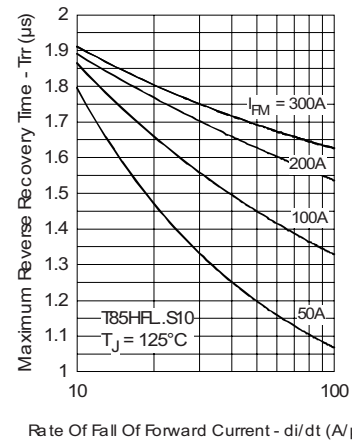


Fig. 34 - Recovery Time Characteristics

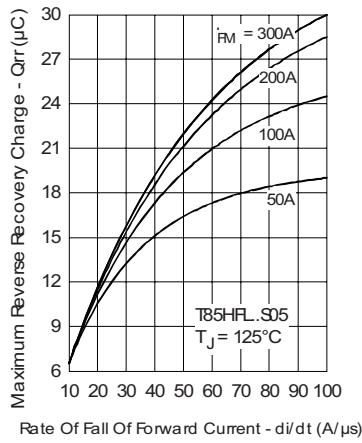


Fig. 32 - Recovery Charge Characteristics

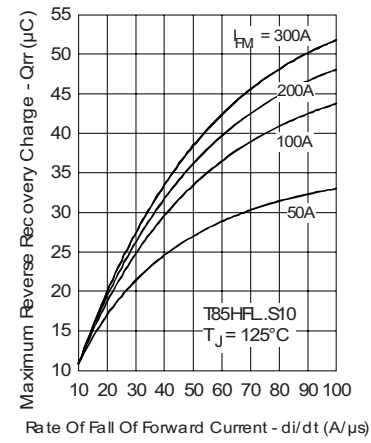


Fig. 35 - Recovery Charge Characteristics

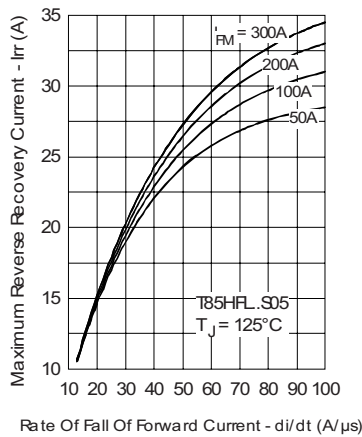


Fig. 33 - Recovery Current Characteristics

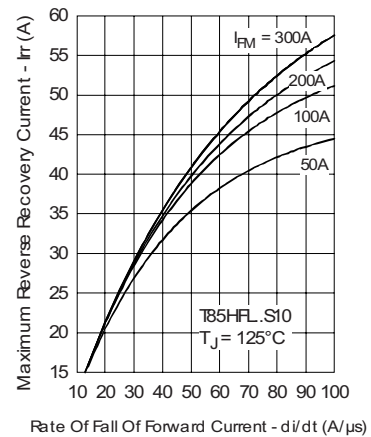


Fig. 36 - Recovery Current Characteristics

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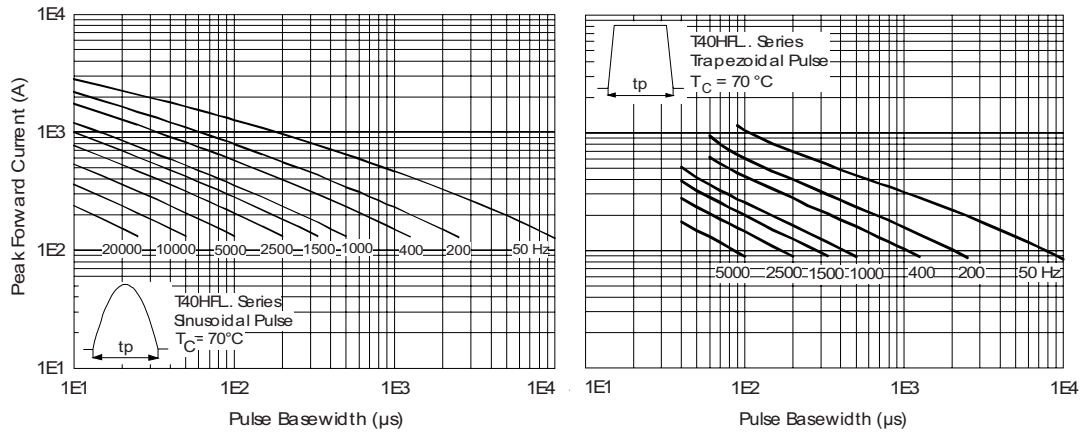


Fig. 37 - Frequency Characteristics

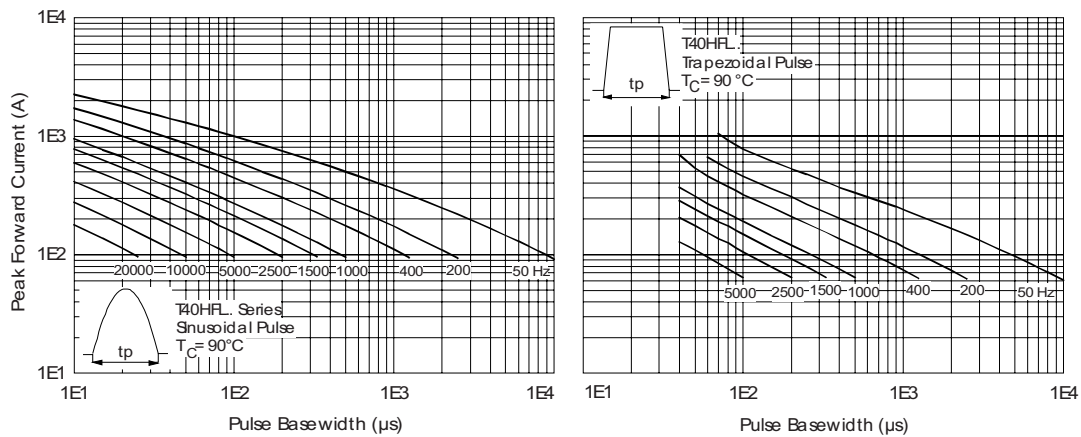


Fig. 38 - Frequency Characteristics

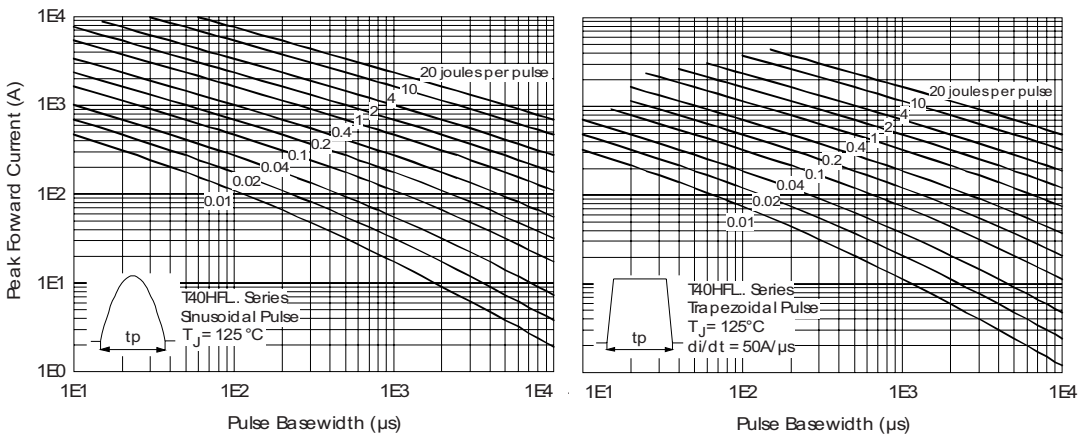


Fig. 39 - Maximum Forward Energy Power Loss Characteristics



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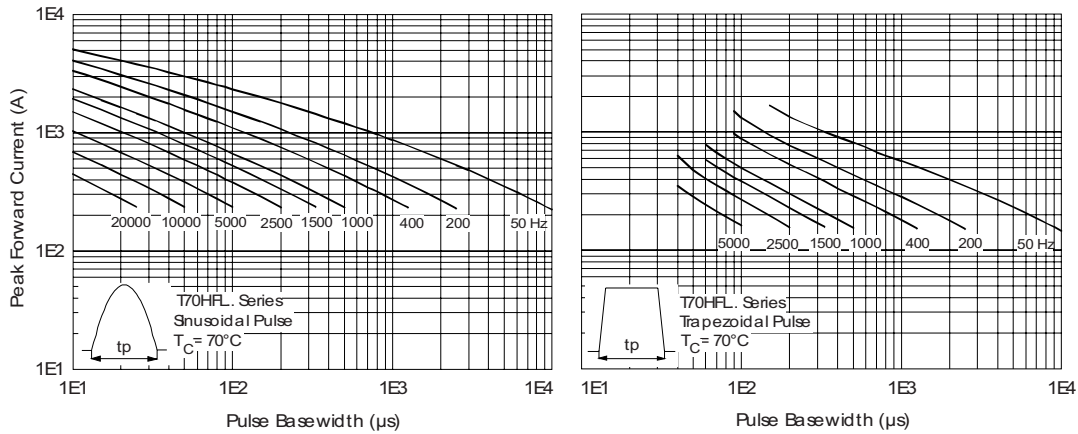


Fig. 40 - Frequency Characteristics

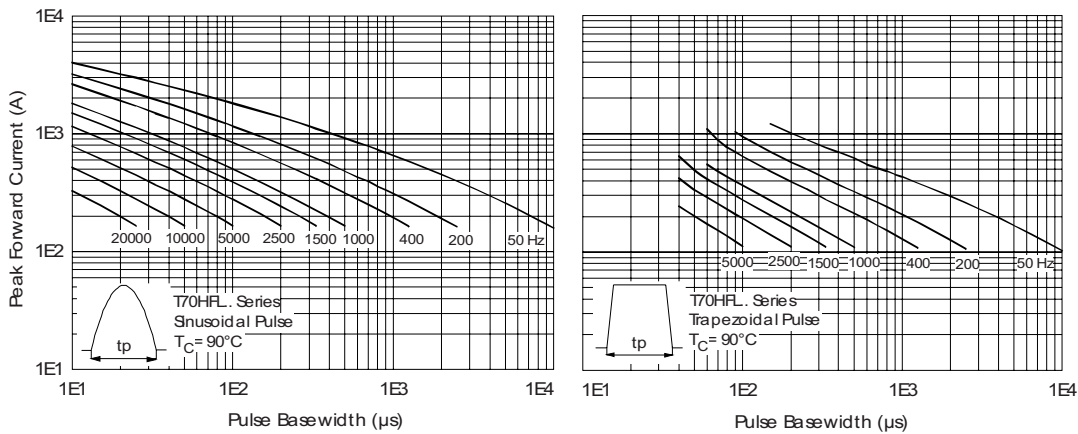


Fig. 41 - Frequency Characteristics

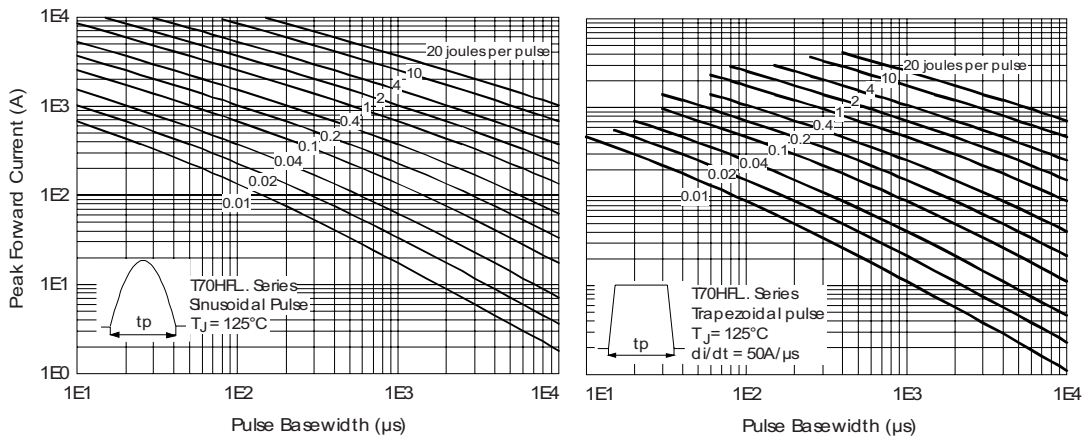


Fig. 42 - Maximum Forward Energy Power Loss Characteristics

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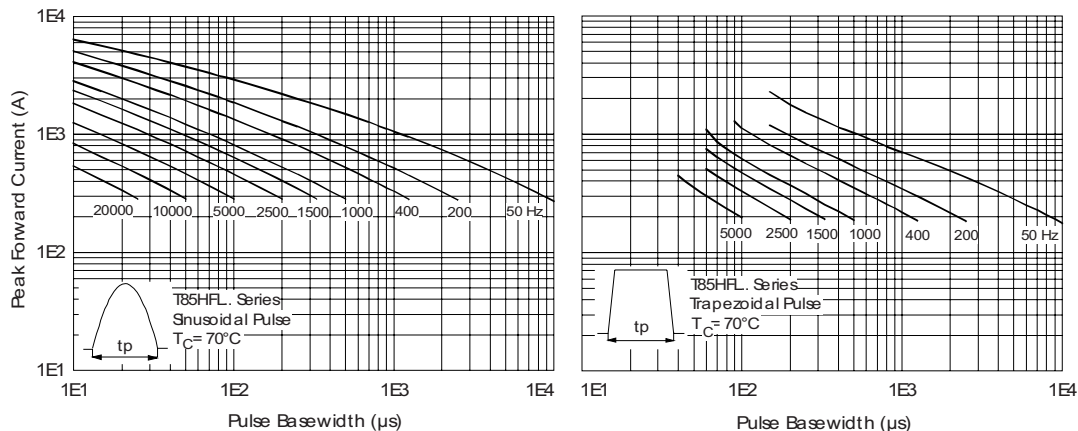


Fig. 43 - Frequency Characteristics

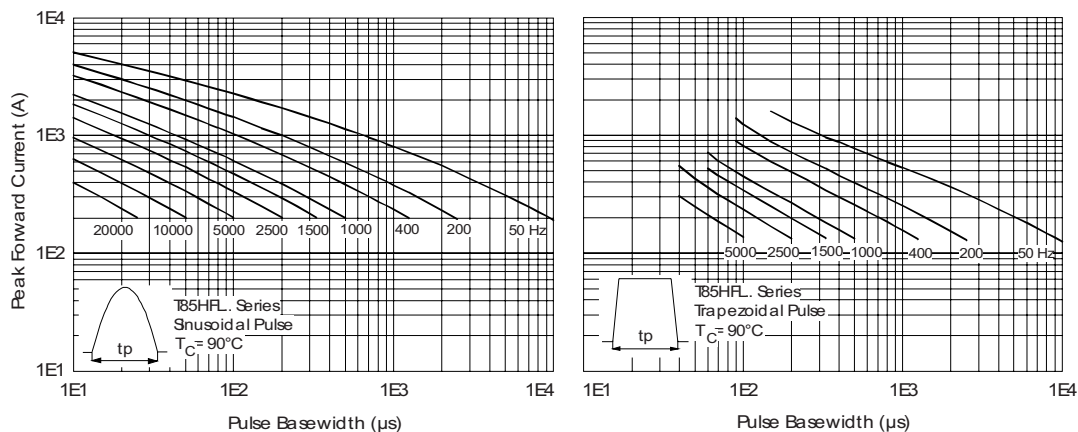


Fig. 44 - Frequency Characteristics

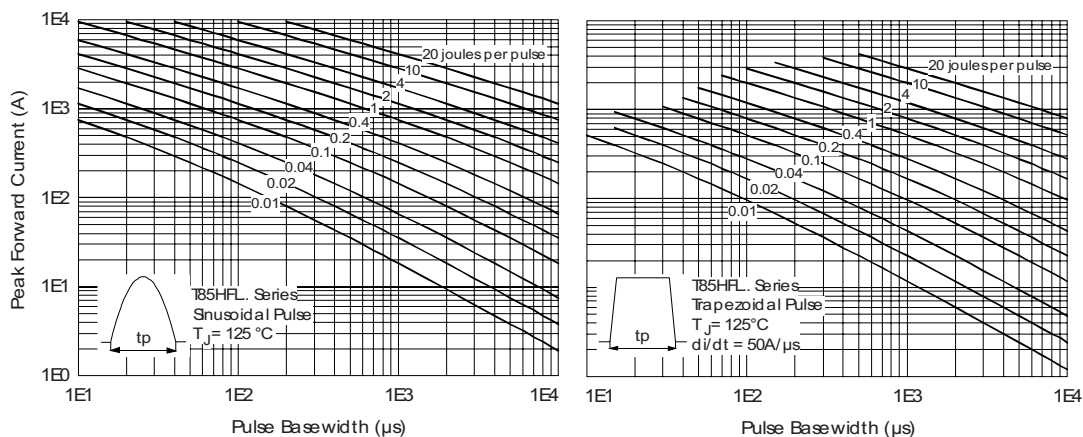


Fig. 45 - Maximum Forward Energy Power Loss Characteristics



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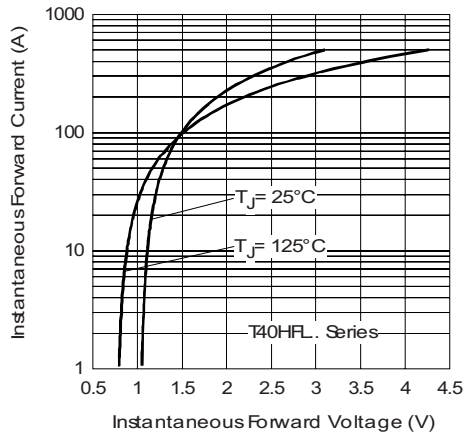


Fig. 46 - Forward Voltage Drop Characteristics

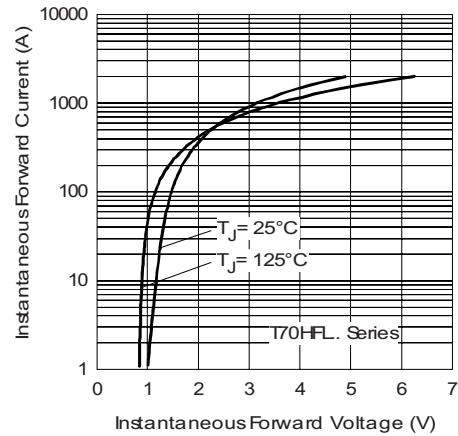


Fig. 47 - Forward Voltage Drop Characteristics

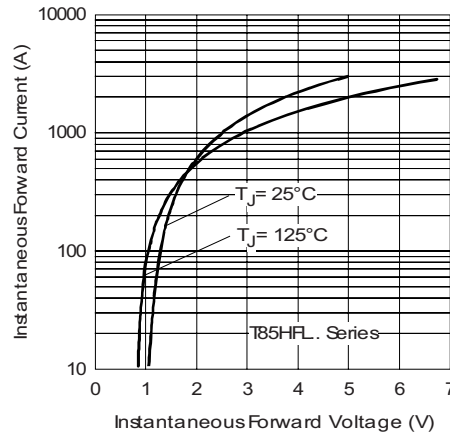


Fig. 48 - Forward Voltage Drop Characteristics

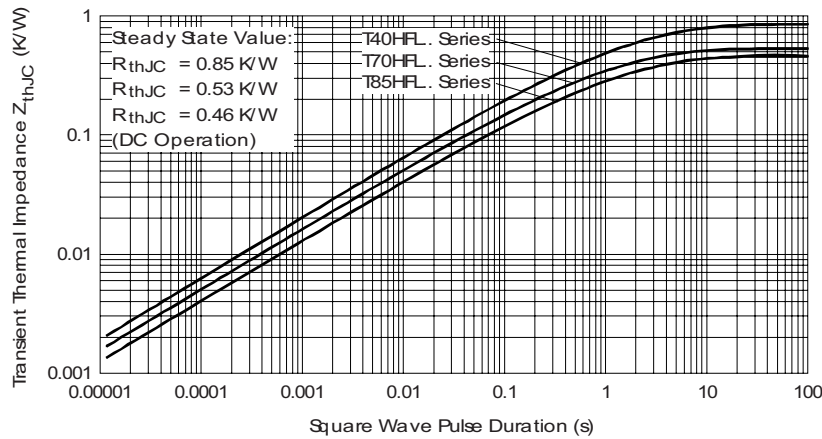


Fig. 49 - Thermal Impedance Z_{thJC} Characteristics

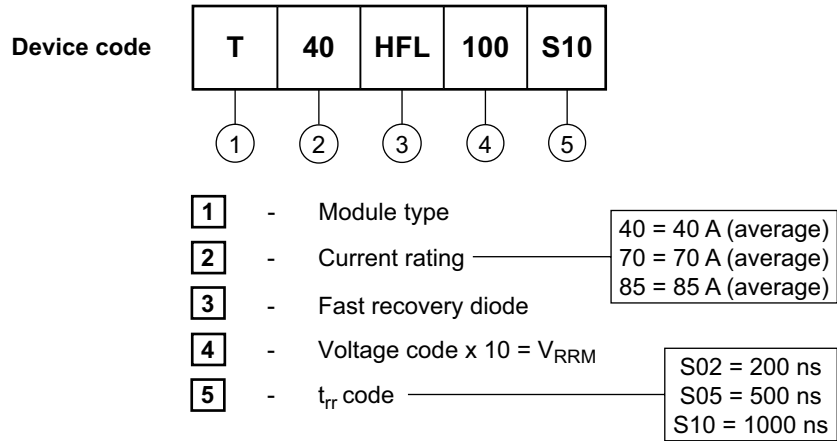
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(T-Modules), 40 A/70 A/85 A

ORDERING INFORMATION TABLE

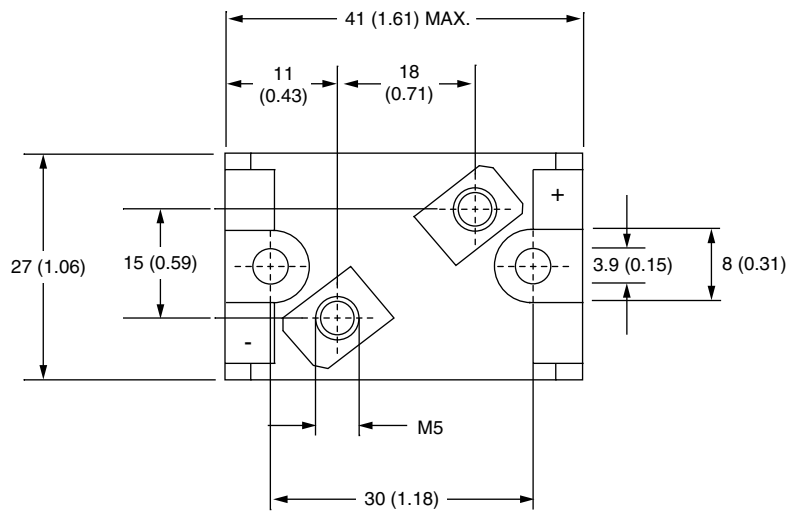
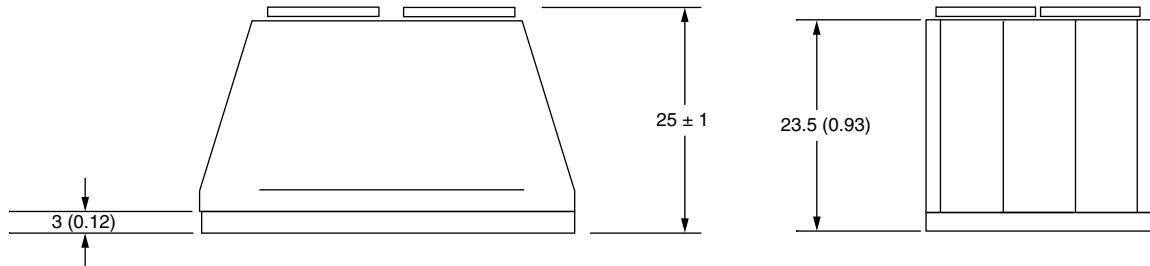


CIRCUIT CONFIGURATION		
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Single switch diode	N/A	

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95313

D-55 T-Module Diode Standard and Fast Recovery

DIMENSIONS in millimeters (inches)





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Поставка электронных компонентов

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Информационное письмо

Компания «ТаймЧипс» - одна из наиболее динамично развивающихся компаний в сфере поставок электронных компонентов. Мы поставляем широкую номенклатуру электронных компонентов отечественных и импортных производителей, как напрямую, так и с крупных мировых складов, позволяющих охватить выборочную номенклатуру более 300 брендов, а также специализируемся на поставках дисплеев и является официальным дистрибьютором компании Shenzhen Startek Electronic Technology Co, на территории Российской Федерации.

Наличие собственной логистики позволяет в кратчайшие сроки доставлять товар нашим клиентам. В нашей компании имеется Конструкторский отдел, где наши специалисты проводят технические консультации клиентов, квалифицированную поддержку и помощь российским разработчикам. Осуществляем Поставки импортной продукции под контролем ВП МО РФ, на предприятия Оборонно-промышленного комплекса России. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001-2011.

Благодаря нацеленности на результат, мы уверенно занимаем новые позиции на рынке, заинтересовывая Клиента не только актуальными ценами и гибким подходом, но и постоянным вниманием.

Миссия – обеспечение долгосрочного и взаимовыгодного партнерства с клиентами.

Наша цель – Обеспечение клиентам самого широкого ассортимента электронных компонентов и бесперебойности поставок.

Мы - это развитие! Мы задаем темп! Мы разные, но вместе! Мы работаем для вас!

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TAI-SAW Пав-компоненты (www.taisaw.com)

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Mini Circuits ВЧ-СВЧ-компоненты (minicircuits.com)

SAMTEC- разъемы (www.samtec.com)

4Star Разъемы РЧ (Даташиты по продукции 4Star, которые Вы сможете загрузить по этой ссылке: <https://yadi.sk/i/tPjnmGGrpmbYj>)

ULNION Преобразователи напряжения (converterdc.com/)

Отличные рекомендации на рынке, уверенность в качестве поставляемой продукции делают нас надежными партнерами для наших клиентов.

«ТаймЧипс» - это:

- Гарантия качества поставляемой продукции;
- Широкий ассортимент;
- Минимальные сроки поставок;
- Техническая поддержка;
- Подбор комплектации;
- Индивидуальный подход;
- Гибкие цены.

Модули, микросхемы, пассивные компоненты, Xilinx (XC), Altera (EP,EPF, EPM) и силовая электроника – это наши ведущие позиции, на поставку которых мы гарантированно дадим Вам самые выгодные предложения!

В структуру компании так же входит конструкторский отдел, который помогает разработчикам и конструкторам в решении следующих задач:

- Оценка стоимости проекта по компонентам;
- Подбор оптимального решения при выборе компонента;
- Подбор аналогов;
- Техническая поддержка;
- Консультации у производителей;
- Поставка прототипов;

С Уважением, Чернов Павел.

Руководитель отдела продаж ООО "ТАЙМЧИПС"

Официальный дистрибьютор Shenzhen Startek Electronic Technology Co.,Ltd в России (USB Display Modules , LED Displays, Serial Modules).

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